

L Number	Hits	Search Text	DB	Time stamp
-	69	(438/722).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/13 11:07
-	69	(("438/722").CCLS.) and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/05/21 15:27
-	223162	438/\$.ccls. or 257/\$.ccls. and @ad<=20010113	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/25 16:06
-	35716	(438/\$.ccls. or 257/\$.ccls. and @ad<=20010113) and 'dielectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/14 14:15
-	4864	((438/\$.ccls. or 257/\$.ccls. and @ad<=20010113) and 'dielectric') and 'mosfet'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/14 14:12
-	1	((438/\$.ccls. or 257/\$.ccls. and @ad<=20010113) and 'dielectric') and 'mosfet') and 'group IV metal'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/14 14:14
-	16571	(438/\$.ccls. or 257/\$.ccls. and @ad<=20010113) and 'dielectric layer'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/14 14:21
-	61	((438/\$.ccls. or 257/\$.ccls. and @ad<=20010113) and 'dielectric layer') and 'hafnium' and 'lanthanum'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/27 16:46
-	104	((438/\$.ccls. or 257/\$.ccls. and @ad<=20010113) and 'dielectric') and 'hafnium' and 'lanthanum'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/14 14:25
-	36	((438/\$.ccls. or 257/\$.ccls. and @ad<=20010113) and 'dielectric') and 'amorphous oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/14 14:26
-	1	((438/\$.ccls. or 257/\$.ccls. and @ad<=20010113) and 'dielectric') and 'hafnium' and 'lanthanum' and 'amorphous oxides'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/14 14:26
-	224025	438/\$.ccls. or 257/\$.ccls. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/25 11:50
-	15	(438/\$.ccls. or 257/\$.ccls. and @ad<=20010613) and 'mosfet' and 'dielectric metal oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/15 10:49
-	4906	(438/\$.ccls. or 257/\$.ccls. and @ad<=20010613) and 'mosfet' and 'dielectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/15 10:51

-	73	((438/.cccls. or 257/.cccls. and @ad<=20010613) and 'mosfet' and 'dielectric') and 'hafnium'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 15:23
-	24	((438/.cccls. or 257/.cccls. and @ad<=20010613) and 'mosfet' and 'dielectric') and 'hafnium') and 'lanthanum'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/15 10:55
-	2	("6020024").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/15 11:22
-	4	("4432035").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/15 13:44
-	417	(257/411).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/12 14:07
-	5	((257/411).CCLS.) and 'hafnium' and 'lanthanum'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/15 13:46
-	230368	438/.cccls. or 257/.cccls. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 11:54
-	168	(438/.cccls. or 257/.cccls. and @ad<=20010613) and 'hafnium' and 'lanthanum'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/23 12:14
-	2	(438/.cccls. or 257/.cccls. and @ad<=20010613) and 'hafnium' and 'combining' with 'oxygen'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 12:02
-	91	(438/.cccls. or 257/.cccls. and @ad<=20010613) and 'hafnium' with 'oxygen'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 12:07
-	67	'hafnium' with 'reaction' with 'oxygen'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 12:32
-	3	'hafnium oxide' near 'formation'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 12:33
-	58	(438/.cccls. or 257/.cccls. and @ad<=20010613) and 'silicon oxide' and 'hafnium' and 'lanthanum'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 15:42
-	51	(438/.cccls. or 257/.cccls. and @ad<=20010613) and 'metal' with 'reduces' with 'silicon oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 13:42

	199	(438/785).ccls. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/12 14:07
	51	((438/785).ccls. and @ad<=20010613) and 'Hf'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/25 14:05
	32	((438/785).ccls. and @ad<=20010613) and 'Hafnium'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/05/21 14:07
	4	("4432035").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/25 14:32
	1	"2693629".PN.	USPAT	2002/06/25 14:35
	1	"3819990".PN.	USPAT	2002/06/25 14:35
	1	"4062749".PN.	USPAT	2002/06/25 14:38
	1	"4227944".PN.	USPAT	2002/06/25 14:38
	1	"5106827".PN.	USPAT	2002/06/25 15:21
	1	"5106827".PN.	USPAT	2002/06/25 15:21
	1	"5187638".PN.	USPAT	2002/06/25 15:21
	1	"5188902".PN.	USPAT	2002/06/25 15:21
	1	"5273927".PN.	USPAT	2002/06/25 15:22
	1	"6177361".PN.	USPAT	2002/06/25 15:22
	1	"5824590".PN.	USPAT	2002/06/25 15:22
	1	"5773314".PN.	USPAT	2002/06/25 15:22
	1	"5572052".PN.	USPAT	2002/06/25 15:22
	90	((438/\$.ccls. or 257/\$.ccls. and @ad<=20010613) and 'mosfet' and 'dielectric') and 'hafnium'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/25 16:05
	0	@ad<=20010613 and 'reduces' with 'silicon dioxide to silicon'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/25 15:44
	1028	@ad<=20010613 and 'reduces' with 'silicon dioxide' with 'silicon'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/25 15:47
	29	@ad<=20010613 and 'reduces' adj 'silicon dioxide' with 'silicon'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/25 16:01
	4	@ad<=20010613 and 'hafnium' adj 'silicon dioxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/25 15:55

-	1	@ad<=20010613 and 'hafnium' adj 'silicon oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/06 09:16
-	126214	438/\$.ccls. or 257/\$.ccls. and @ad<=20010113 and 'high dielectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/25 16:09
-	124737	438/\$.ccls. or 257/\$.ccls. and @ad<=20010113 and 'high dielectric' and 'silicon oxide' and 'hafnium'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/11 08:52
-	31	@ad<=20010113 and 'PVD' with 'ion bombardment'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/11 11:45
-	393	@ad<=20010113 and 'high dielectric' and 'physical vapor deposition' or 'PVD' with 'ion bombardment'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/11 09:01
-	393	@ad<=20010113 and 'high dielectric' and 'physical vapor deposition' or 'PVD' with 'ion bombardment energy'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/11 09:04
-	13419	@ad<=20010113 and 'high dielectric constant'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/11 09:08
-	332	(@ad<=20010113 and 'high dielectric constant') and 'physical vapor deposition'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/11 09:09
-	0	((@ad<=20010113 and 'high dielectric constant') and 'physical vapor deposition') and 'ion bombardment energy'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/11 09:10
-	16	((@ad<=20010113 and 'high dielectric constant') and 'physical vapor deposition') and 'ion bombardment'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/11 09:10
-	1	"4495219".PN.	USPAT	2002/07/11 10:00
-	1	"6013553".PN.	USPAT	2002/07/11 10:00
-	1	"6015739".PN.	USPAT	2002/07/11 10:00
-	1	"5464792".PN.	USPAT	2002/07/11 10:00
-	1	"6020024".PN.	USPAT	2002/07/11 10:01
-	1	"6020243".PN.	USPAT	2002/07/11 10:01
-	1	"6060755".PN.	USPAT	2002/07/11 10:01
-	1	"6110784".PN.	USPAT	2002/07/11 10:01
-	6	@ad<=20010113 and 'hafnium deposition'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/11 11:46

	22	@ad<=20010113 and 'hafnium' and 'PVD' and 'ion bombardment'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/11 11:52
	3	@ad<=20010113 and 'hafnium' and 'PVD' and 'ion bombardment' and 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/11 11:51
	3	@ad<=20010113 and 'hafnium' and 'sputtering' and 'ion bombardment' with 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/06 09:10
	53	@ad<=20010113 and 'metal' and 'sputtering' and 'ion bombardment' with 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/11 12:56
	1	"4520413".PN.	USPAT	2002/07/11 13:08
	1	"5930611".PN.	USPAT	2002/07/11 13:08
	1	"6054331".PN.	USPAT	2002/07/11 13:09
	1	"6060391".PN.	USPAT	2002/07/11 13:11
	1	"6069070".PN.	USPAT	2002/07/11 13:12
	266	@ad<=20010113 and 'hafnium' with 'sputtering'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/11 13:15
	22	@ad<=20010113 and 'hafnium' and 'PVD' and 'ion bombardment'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/23 12:01
	22	@ad<=20010613 and 'hafnium' and 'PVD' and 'ion bombardment'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/23 12:09
	1	"4173661".PN.	USPAT	2002/07/23 12:08
	1	"5773363".PN.	USPAT	2002/07/23 12:08
	5	@ad<=20010613 and 'hafnium' and 'PVD' and 'ion bombardment' with 'energy'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/23 13:16
	6	@ad<=20010613 and 'PVD' and 'ion bombardment' with 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/23 12:40
	3	@ad<=20010613 and 'hafnium' and 'ion bombardment' with 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/23 12:52
	29	@ad<=20010613 and 'PVD' and 'oxygen radical'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/23 12:38

	67	@ad<=20010613 and 'sputter' and 'oxygen radical'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 12:39
	19	@ad<=20010613 and 'hafnium' and 'sputter' with 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 12:50
	4	@ad<=20010613 and 'hafnium' and 'sputter' and 'oxygen radical' with 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 12:44
	6	@ad<=20010613 and 'hafnium' and 'Ionized' with 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 12:50
	14	@ad<=20010613 and 'hafnium' and 'ion bombardment' and 'sputter' and 'ev'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 13:01
	912	@ad<=20010613 and 'dielectric deposition'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 13:10
	118	(@ad<=20010613 and 'dielectric deposition') and 'refractory metal'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 13:09
	1	((@ad<=20010613 and 'dielectric deposition') and 'refractory metal') and 'sputter' and 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 13:09
	0	((@ad<=20010613 and 'dielectric deposition') and 'refractory metal') and 'PVD' and 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 13:09
	12	(@ad<=20010613 and 'dielectric deposition') and 'hafnium'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 13:09
	6	@ad<=20010613 and 'hafnium deposition'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 13:15
	96	@ad<=20010613 and 'ion bombardment' with 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 13:19
	3	(@ad<=20010613 and 'ion bombardment' with 'eV' ) and 'hafnium'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 13:20
	2	("6399521").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 14:33

-	78	((438/\$.cccls. or 257/\$.cccls. and @ad<=20010113) and 'dielectric layer') and 'hafnium' and 'lanthanum'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/23 12:15
-	108	((438/\$.cccls. or 257/\$.cccls. and @ad<=20010113) and 'dielectric layer') and 'hafnium' and 'lanthanum'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/24 08:21
-	8	@ad<=20010113 and 'dielectric layer' and 'hafnium' and 'lanthanum' and 'oxygen' and 'ion bombardment'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/24 08:33
-	29	@ad<=20010113 and 'physical vapor deposition' and 'hafnium' and 'oxygen' and 'ion bombardment'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/24 08:39
-	62	@ad<=20010113 and 'dielectric' and 'physical vapor deposition' and 'ion bombardment' same 'energy'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/24 08:40
-	120	@ad<=20010113 and 'physical vapor deposition' and 'ion bombardment' same 'energy'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/24 08:40
-	14	@ad<=20010113 and 'hafnium' and 'physical vapor deposition' and 'ion bombardment' same 'energy'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/24 08:53
-	2	@ad<=20010113 and 'lanthanum' and 'physical vapor deposition' and 'ion bombardment' same 'energy'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/24 08:41
-	14	@ad<=20010113 and 'physical vapor deposition' same 'hafnium oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/24 08:45
-	4	@ad<=20010113 and 'hafnium' and 'electron beam evaporation' and 'ion bombardment' and '10 eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/24 08:59
-	3	@ad<=20010113 and 'lanthanum' and 'electron beam evaporation' and 'ion bombardment' and '10 eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/24 09:37
-	2	@ad<=20010113 and 'lanthanum' and 'hafnium' and 'oxygen radical'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/24 09:40
-	2	("6387761").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 13:36
-	2	("6159855").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 13:38

-	2	("6013553").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 13:38
-	2178	@ad<=20010613 and 'Hafnium' same 'Lanthanum'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 16:05
-	52	@ad<=20010613 and 'dielectric' with 'Hafnium' same 'Lanthanum'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 09:17
-	39	@ad<=20010613 and 'first' with 'Hf' same 'second' with 'La'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 14:42
-	274	@ad<=20010613 and 'first' with 'Group IV' and 'second' with 'Group III'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 14:45
-	16	@ad<=20010613 and 'first' with 'Group IVB' and 'second' with 'Group IIIB'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 15:06
-	243	(438/785).CCLS. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 15:35
-	83	(438/722).CCLS. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 15:31
-	457	(257/411).CCLS. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 15:31
-	597	(257/310).CCLS. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/12 14:08
-	461	(257/410).CCLS. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/12 14:08
-	158	(438/635).CCLS. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/12 14:09
-	627	(438/778).CCLS. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/12 14:10
-	400	(438/758).CCLS. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/12 14:10

	457	(257/411).CCLS. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/05/21 15:36
	631	(438/240).ccls. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/12 14:11
	102	(438/216).ccls. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/12 14:11
	275	(438/591).ccls. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/12 14:12
	739	(438/585).ccls. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/12 14:13
	170	@ad<=20010613 and 'Hafnium oxide' with 'Lanthanum oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/06 09:11
	2	"20010013629"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/05 14:41
	2	"20020192974"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/05 14:41
	65	@ad<=20010613 and 'silicon oxide' with 'Hafnium' with 'Lanthanum'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/06 09:05
	4	(("6159855") or ("6013553")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/06 09:05
	3	@ad<=20010113 and 'hafnium' and 'sputtering' and 'ion bombardment' with 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/06 09:10
	39	@ad<=20010613 and 'MOS' and 'Hafnium oxide' with 'Lanthanum oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/06 09:11
	2	@ad<=20010613 and 'hafnium' adj 'silicon oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/06 09:16
	58	@ad<=20010613 and 'dielectric' with 'Hafnium' same 'Lanthanum'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/06 10:12



-	2	("6573197").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/13 12:38
-	2	("6184072").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/13 12:38